CLAIM AMENDMENTS

1. (Currently Amended) A method ~~for~~ of forming a porous film comprising ~~the steps of~~:

applying a film-forming composition containing a polysiloxane, a pore-forming agent, an onium salt, and a solvent onto a substrate,

~~subjecting a first heat treatment for~~ evaporating said solvent from said film-forming composition in a first heat treatment,

~~subjecting a second heat treatment for~~ promoting ~~the~~ polymerization of said polysiloxane in an inert-gas atmosphere in a second heat treatment, and

~~subjecting a third heat treatment for~~ vaporizing said pore-forming agent in an oxidizing-gas ~~atmosphere~~ ambient in a third heat treatment.

2. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 1, ~~wherein said~~ including evaporating the solvent in the first heat-treatment ~~is carried out~~ in an inert-gas atmosphere at a temperature ~~of~~ not exceeding 350°C ~~or below~~.

3. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 1, ~~wherein said~~ including promoting polymerization in the second heat-treatment ~~is carried out~~ at a temperature ~~of~~ not exceeding 400°C ~~or below~~.

4. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 1, ~~wherein said~~ including promoting polymerization in the second heat-treatment ~~is carried out~~ at a temperature ~~of~~ not exceeding 350°C ~~or below~~.

5. (Currently Amended) The method ~~for~~ forming a porous film according to claim 1, ~~wherein said~~ including vaporizing said pore-forming agent in the third heat-treatment ~~is carried out~~ at a temperature ~~equal to or lower than~~ not exceeding the temperature in ~~said~~ promoting polymerization in the second heat-treatment.

6. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 1, wherein said oxidizing-gas ~~is~~ ambient includes oxygen ~~gas~~.

7. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 6, wherein said oxygen ~~gas~~ contains one of ozone ~~or~~ and oxygen radicals.

8. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 1, wherein said polysiloxane is a hydrolytic condensation product of a compound represented by the general formula (1):

~~[Formula 1]~~

$$R_nSiX_{4-n} \cdots\cdots (1)$$

wherein R represents a hydrogen atom~~,~~ or an organic group having from 1 to 20 carbon atoms, X represents ~~a~~ hydrolysable ~~group~~ groups which may be the same as or different from each other, and n represents an integer from 0 to 2, with the proviso that when n is 2, R may be the same or different moieties.

9. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 8, wherein the weight-average molecular weight of said polysiloxane ranges from 300 to 20,000.

10. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 1, wherein said pore-forming agent is a polymer having an alkylene-oxide structure with a weight-average molecular weight of from 200 to 10,000.

11. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 1, wherein said onium salt is an ammonium salt.

12. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 1, wherein said solvent is selected from the group consisting of an alkylene glycol dialkyl ether ~~or~~ and a dialkylene glycol dialkyl ether.

13. (Currently Amended) The method ~~for~~ of forming a porous film according to claim 1, wherein said substrate is a semiconductor substrate.